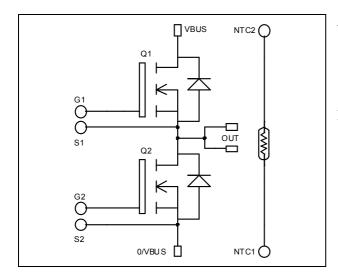


Phase Leg <u>MOSFET Power Module</u>

$$\begin{split} V_{DSS} &= 1200V \\ R_{DSon} &= 290 m \Omega \text{ typ } @ \text{ Tj} = 25^{\circ} \text{C} \\ I_D &= 34 \text{A} @ \text{Tc} = 25^{\circ} \text{C} \end{split}$$



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Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
$V_{ m DSS}$	Drain - Source Breakdown Voltage		1200	V
Ţ	Continuous Drain Current	$T_c = 25^{\circ}C$	34	
I_D	Continuous Diani Current	$T_c = 80$ °C	25	A
I_{DM}	Pulsed Drain current			
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		348	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		780	W
I_{AR}	Avalanche current (repetitive and non repetitive)		22	A
E_{AR}	Repetitive Avalanche Energy		50	m I
E_{AS}	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1200V$	$T_j = 25^{\circ}C$			350	μА
		$V_{GS} = 0V, V_{DS} = 1000V$	$T_j = 125$ °C			1500	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 17A$			290	348	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 5mA$		3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$				±150	nA

Dynamic Characteristics

·	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		10.3		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		1.54		nF
C_{rss}	Reverse Transfer Capacitance	f=1MHz		0.26		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		374		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 600V$		48		nC
$Q_{gd} \\$	Gate – Drain Charge	$I_D = 34A$		240		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		20		ns
$T_{\rm r}$	Rise Time	$V_{GS} = 15V$ $V_{GS} = 200V$		15		
$T_{d(off)}$	Turn-off Delay Time	$\begin{array}{c} \begin{array}{c} \begin{array}{c} \\ \\ \\ \end{array} \\ \begin{array}{c} \\ \\ \\ \\ \end{array} \\ \\ \begin{array}{c} \\ \\ \\ \\ \end{array} \\ \begin{array}{c} \\ \\ \\ \\ \\ \\ \end{array} \\ \begin{array}{c} \\ \\ \\ \\ \\ \\ \end{array} \\ \\ \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \end{array} \\ \begin{array}{c} \\ \\ \\ \\ \\ \\ \end{array} \\ \\ \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \end{array} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $		160		
T_{f}	Fall Time	$R_G = 2.5\Omega$		45		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V$, $V_{Bus} = 800V$ $I_D = 34A$, $R_G = 2.5\Omega$		1980		1
E_{off}	Turn-off Switching Energy			1371		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		3131		T
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		1714		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$			34	Α
	(Body diode)		$Tc = 80^{\circ}C$			25	А
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V$, $I_S = -34A$	1			1.3	V
dv/dt	Peak Diode Recovery					18	V/ns
t _{rr}	Reverse Recovery Time	$I_S = -34A$ $-V_R = 600V$ $di_S/dt = 200A/\mu s$	$T_j = 25^{\circ}C$			320	ns
			$T_j = 125$ °C			650	115
Qrr	Reverse Recovery Charge		$T_j = 25^{\circ}C$		4		μC
Qrr	reverse receivery charge		$T_j = 125$ °C		14		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \le$ - 34A $di/dt \le 700 A/\mu s$ $V_R \le V_{DSS}$ $T_j \le 150 ^{\circ} C$



Thermal and package characteristics

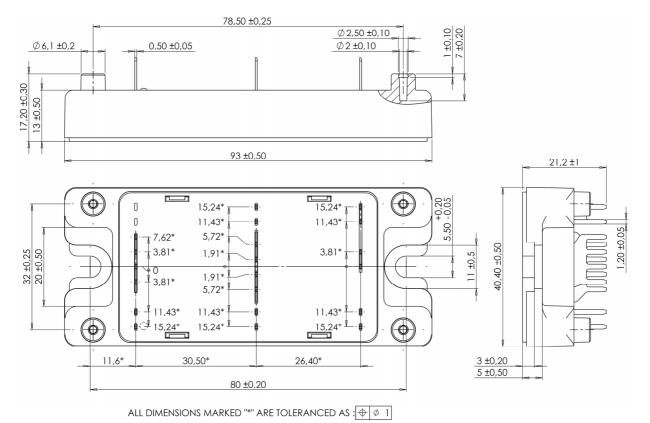
Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance					0.16	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight	_				160	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

 Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature at T

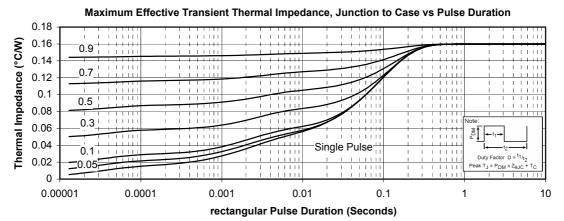
SP4 Package outline (dimensions in mm)

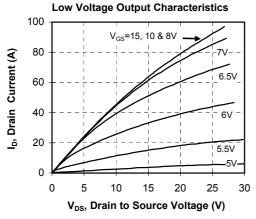


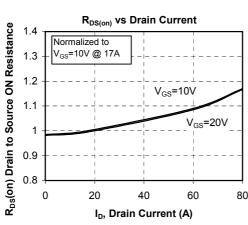
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

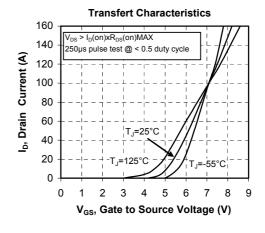


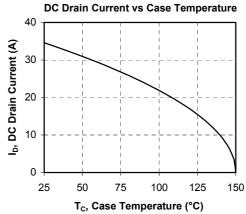
Typical Performance Curve



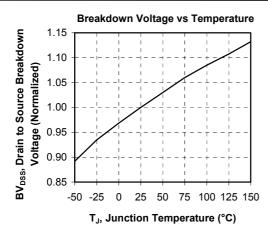


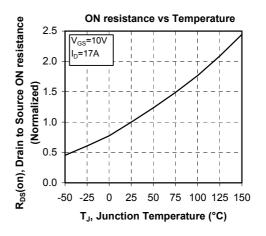


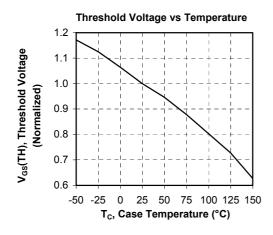


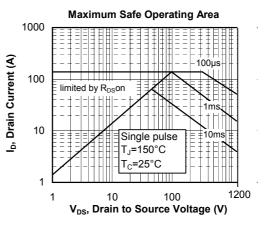


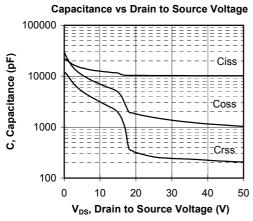


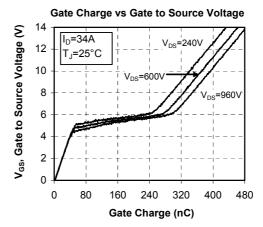




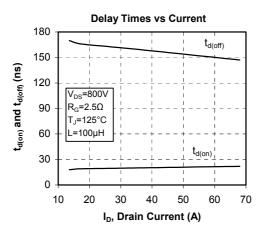


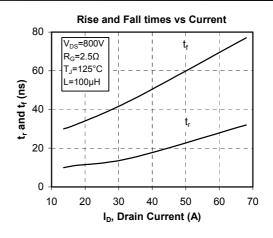


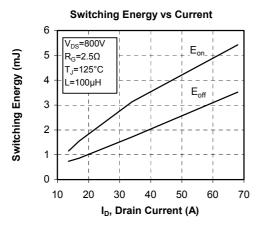


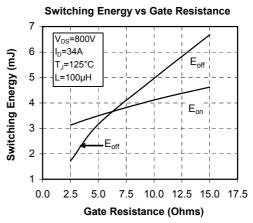


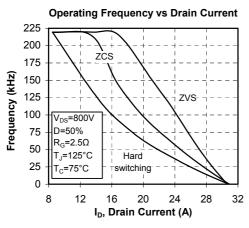


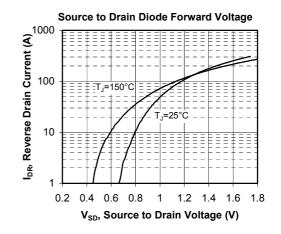














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